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March 2015

FDD2670

FDD2670

200V N-Channel PowerTrench® MOSFET

General Description

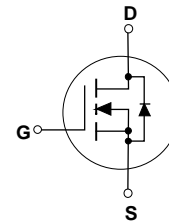
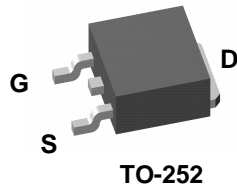
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 3.6 A, 200 V. $R_{DS(ON)} = 130 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$
- Low gate charge
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|---|-------------|------------------|
| V_{DS} | Drain-Source Voltage | 200 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| I_D | Drain Current – Continuous (Note 1) | 3.6 | A |
| | Drain Current – Pulsed | 20 | |
| P_D | Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ (Note 1) | 70 | W |
| | @ $T_A = 25^\circ\text{C}$ (Note 1a) | 3.2 | |
| | @ $T_A = 25^\circ\text{C}$ (Note 1b) | 1.3 | |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 3.2 | V/ns |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|-----|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Note 1) | 1.8 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1b) | 96 | $^\circ\text{C/W}$ |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|---------|-----------|------------|------------|
| FDD2670 | FDD2670 | 13" | 16mm | 2500 units |

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Drain-Source Avalanche Ratings (Note 1)

| | | | | | | |
|-----------|--|---|--|--|-----|----|
| W_{DSS} | Single Pulse Drain-Source Avalanche Energy | $V_{DD} = 100\text{ V}, I_D = 3.6\text{ A}$ | | | 375 | mJ |
| I_{AR} | Maximum Drain-Source Avalanche Current | | | | 3.6 | A |

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|-----|-----|------|----------------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 200 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C | | 214 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| I_{GSSF} | Gate-Body Leakage, Forward | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$ | | | 100 | NA |
| I_{GSSR} | Gate-Body Leakage, Reverse | $V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$ | | | -100 | NA |

On Characteristics (Note 2)

| | | | | | | |
|--|--|---|----|------------|------------|----------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2 | 4 | 4.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C | | -10 | | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10\text{ V}, I_D = 3.6\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 3.6\text{ A}, T_J = 125^\circ\text{C}$ | | 100 205 | 130 275 | m Ω |
| $I_{D(on)}$ | On-State Drain Current | $V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$ | 20 | | | A |
| g_{FS} | Forward Transconductance | $V_{DS} = 5\text{ V}, I_D = 3.6\text{ A}$ | | 15 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|---|--|------|--|----|
| C_{iss} | Input Capacitance | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$ | | 1228 | | PF |
| C_{oss} | Output Capacitance | | | 112 | | PF |
| C_{rss} | Reverse Transfer Capacitance | | | 17 | | pF |

Switching Characteristics (Note 2)

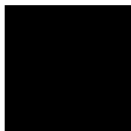
| | | | | | | |
|--------------|---------------------|---|--|----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 100\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$ | | 13 | 23 | ns |
| t_r | Turn-On Rise Time | | | 8 | 16 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 30 | 48 | ns |
| t_f | Turn-Off Fall Time | | | 25 | 40 | ns |
| Q_g | Total Gate Charge | $V_{DS} = 100\text{ V}, I_D = 3.6\text{ A},$ $V_{GS} = 10\text{ V}$ | | 27 | 43 | nC |
| Q_{gs} | Gate-Source Charge | | | 7 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 10 | | nC |

Drain-Source Diode Characteristics and Maximum Ratings

| | | | | | | |
|----------|---|--|--|-----|-----|---|
| I_S | Maximum Continuous Drain-Source Diode Forward Current | | | | 2.1 | A |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 2.1\text{ A}$ (Note 2) | | 0.7 | 1.2 | V |

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $R_{\theta JA} = 40^\circ\text{C/W}$ when mounted on a 1 in² pad of 2oz copper.



b) $R_{\theta JA} = 96^\circ\text{C/W}$ on a minimum mounting pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

3. $I_{SD} \leq 3\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

Typical Characteristics

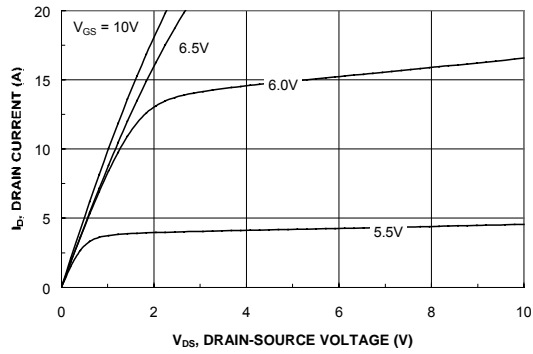


Figure 1. On-Region Characteristics.

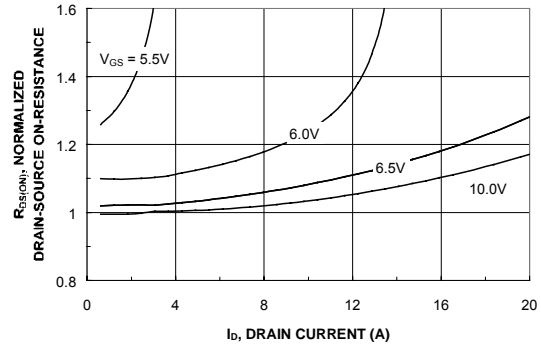


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

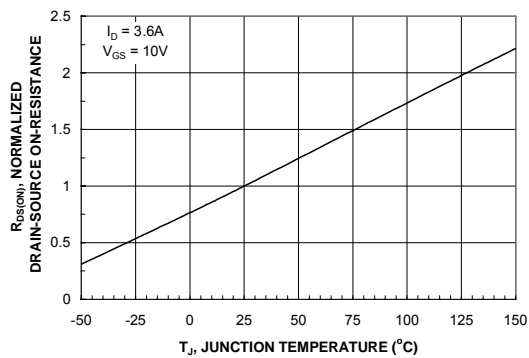


Figure 3. On-Resistance Variation with Temperature.

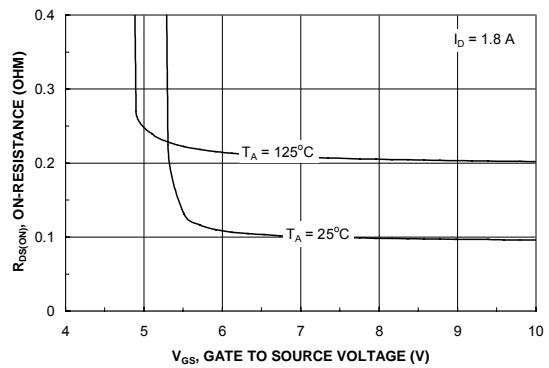


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

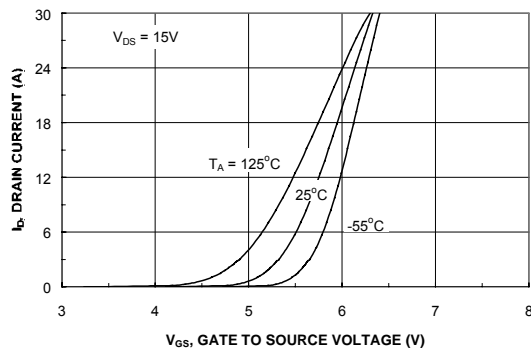


Figure 5. Transfer Characteristics.

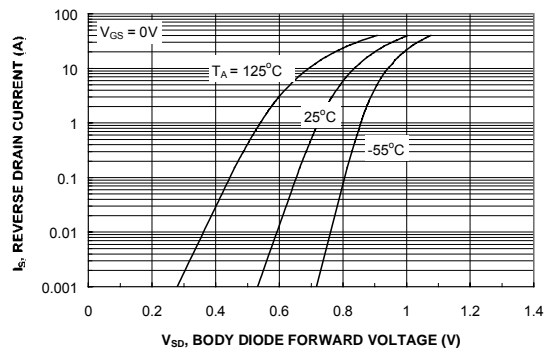


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

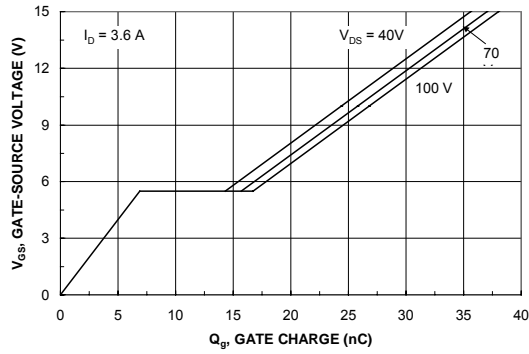


Figure 7. Gate Charge Characteristics.

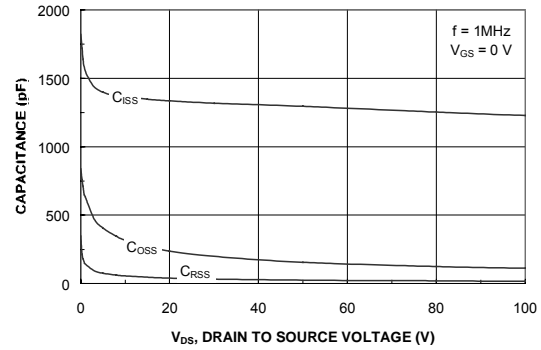


Figure 8. Capacitance Characteristics.

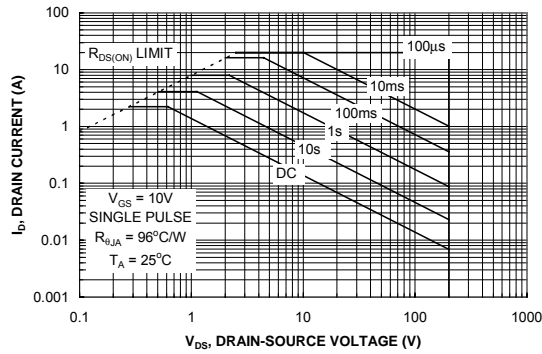


Figure 9. Maximum Safe Operating Area.

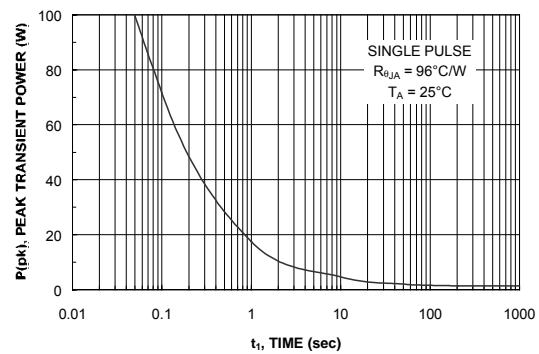


Figure 10. Single Pulse Maximum Power Dissipation.

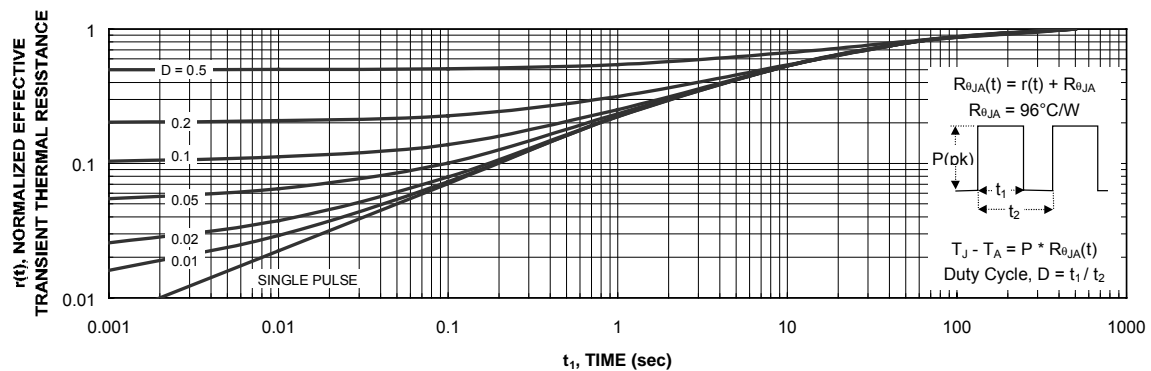
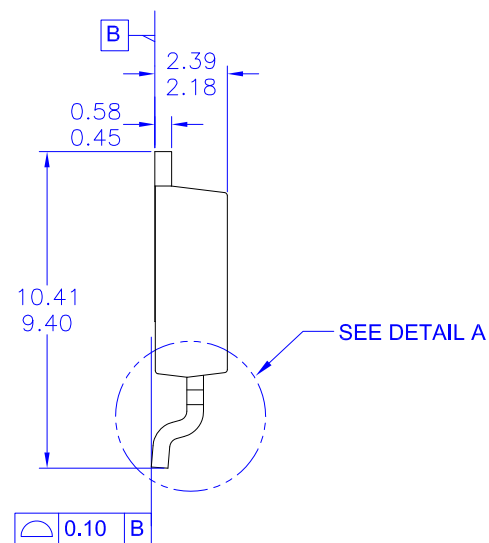
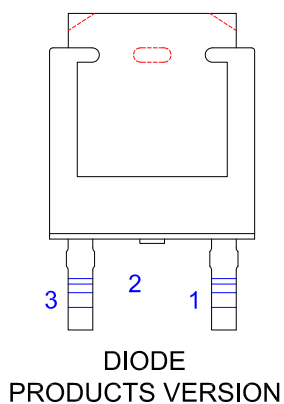
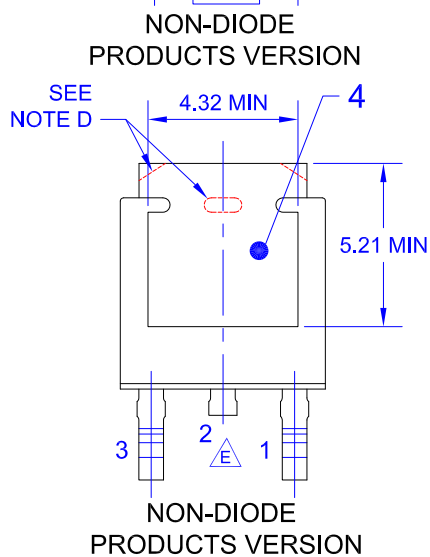
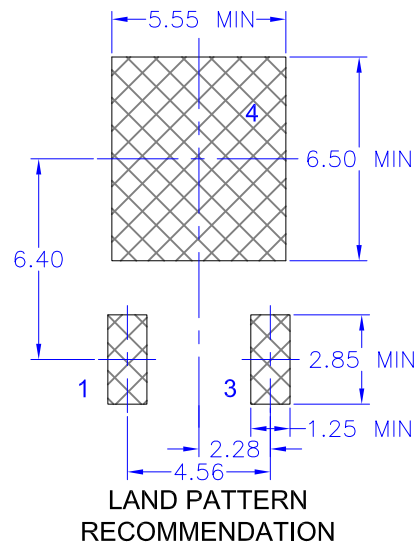
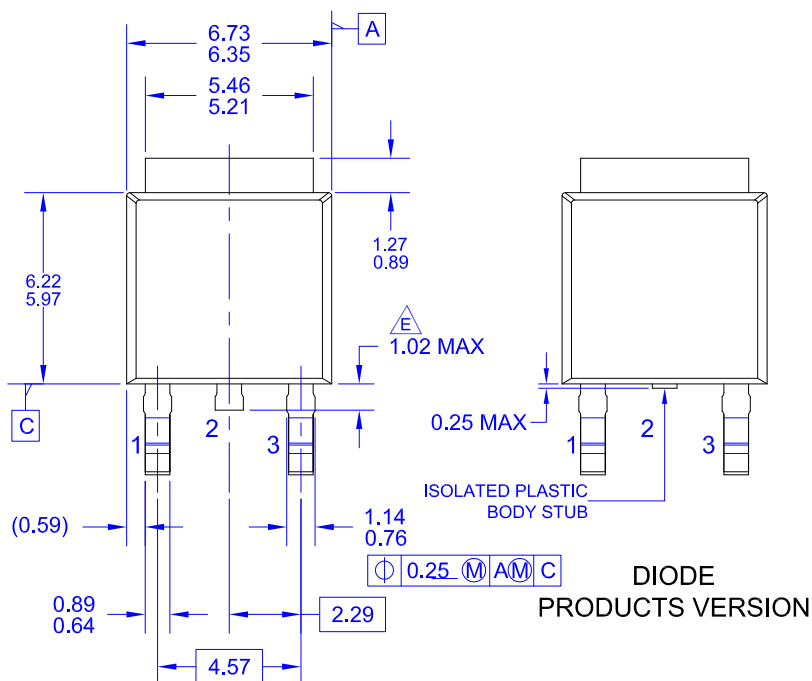


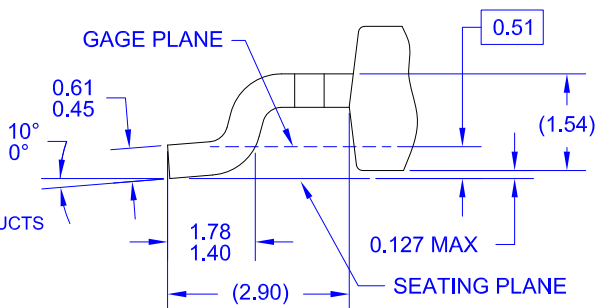
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
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- F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
- H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



DETAIL A
(ROTATED -90°)
SCALE: 12X



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